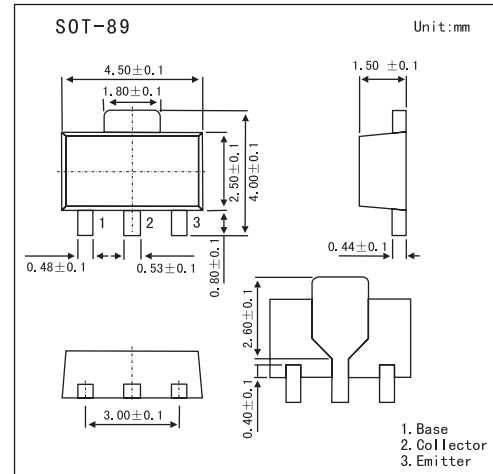


Silicon PNP Epitaxial

2SA1945

■ Features

- High voltage $V_{CE0}=-50V$
- High f_T : $f_T=150MHz$ typ
- Excellent linearity of DC forward current gain
- High collector current $I_{CM}=600mA$
- Small package for mounting

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-55	V
Emitter-base voltage	V_{EB0}	-4	V
Collector-emitter voltage	V_{CE0}	-50	V
Peak collector current	I_{CM}	-600	mA
Collector current	I_C	-400	mA
Collector dissipation ($T_a=25^\circ C$)	P_C	500	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=-10\mu A, I_E=0$	-55			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=-10\mu A, I_C=0$	-4			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C=-100\mu A, R_{BE}=\infty$	-50			V
Collector cutoff current	I_{CB0}	$V_{CB}=-25V, I_E=0$			-1	μA
Emitter cutoff current	I_{EB0}	$V_{EB}=-2V, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-4V, I_C=-100mA$	90		500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-200mA, I_B=-10mA$		-0.17	-0.5	V
Gain bandwidth product	f_T	$V_{CE}=-6V, I_E=-10mA$		150		MHz

■ h_{FE} Classification

Marking	ZD	ZE	ZF
h_{FE}	90~180	150~300	250~500